

SANYO	No.1048B	2SA1252/2SC3134
		PNP/NPN Epitaxial Planar Silicon Transistors For AF Applications

Features

- . High V_{EBO} .
- . Wide ASO and high durability against breakdown.

() : 2SA1252

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Collector to Base Voltage	V_{CB0}	(-)60	V
Collector to Emitter Voltage	V_{CEO}	(-)50	V
Emitter to Base Voltage	V_{EBO}	(-)15	V
Collector Current	I_C	(-)150	mA
Collector Current(Pulse)	I_{CP}	(-)300	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40\text{V}, I_E=0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)10\text{V}, I_C=0$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)6\text{V}, I_C=(-)1\text{mA}$	90*		560*	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)6\text{V}, I_C=(-)1\text{mA}$		100		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)6\text{V}, f=1\text{MHz}$		(3.5)		pF
				2.2		
C to E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)50\text{mA}, I_B=(-)5\text{mA}$			(-)0.5	V
C to B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-)60			V
C to E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-)50			V
E to B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-)15			V

*The 2SA1252/2SC3134 are classified as follows according to h_{FE} at 1mA:

90	4	180	135	5	270	200	6	400	300	7	600
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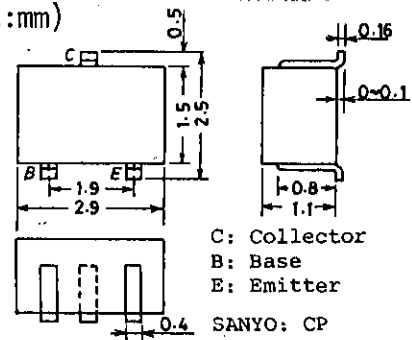
Marking 2SA1252 : D

2SC3134 : H

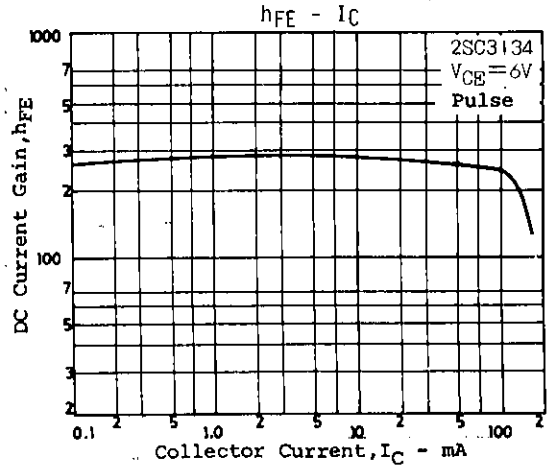
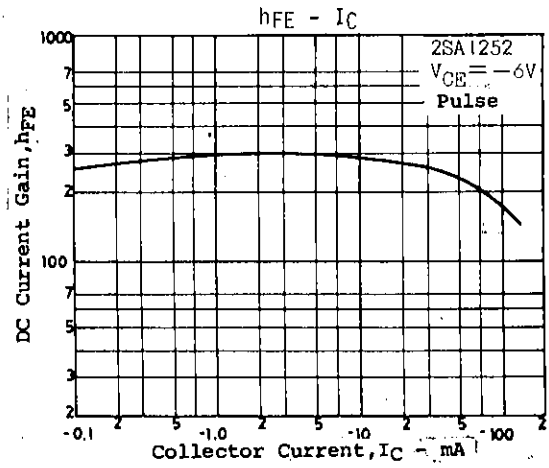
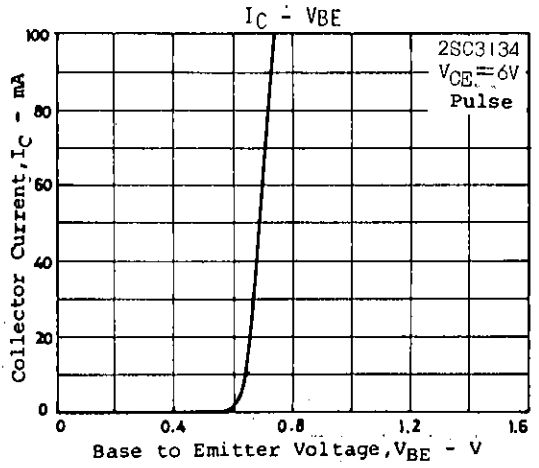
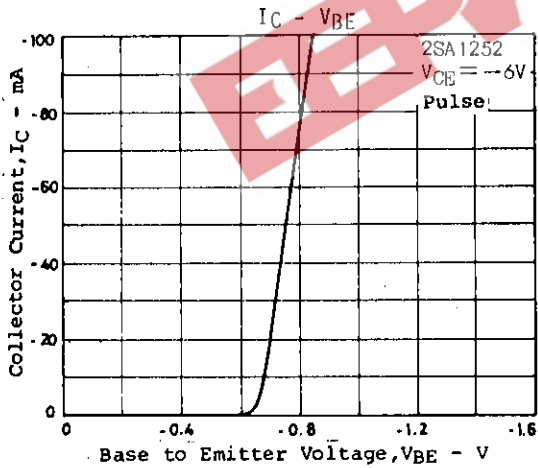
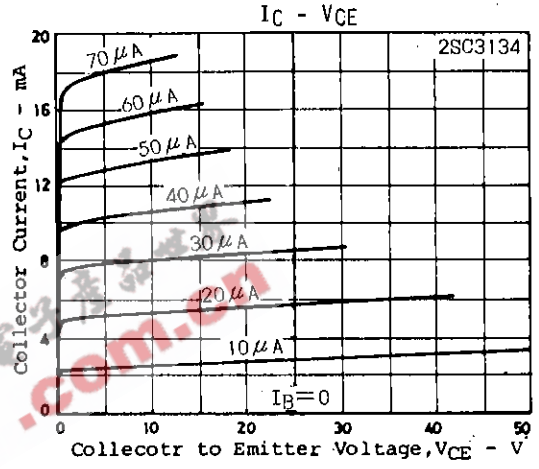
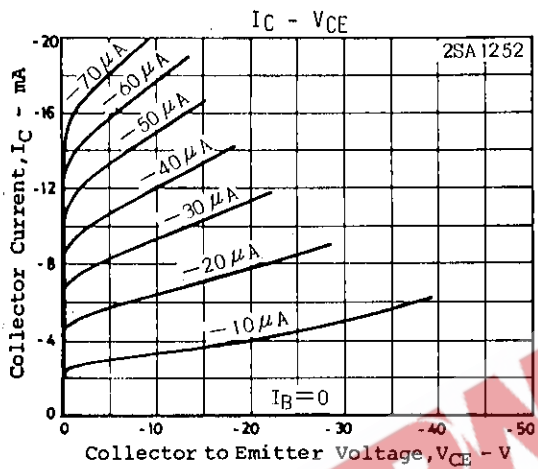
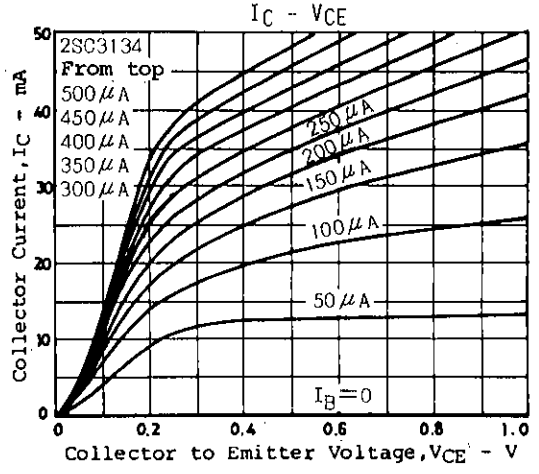
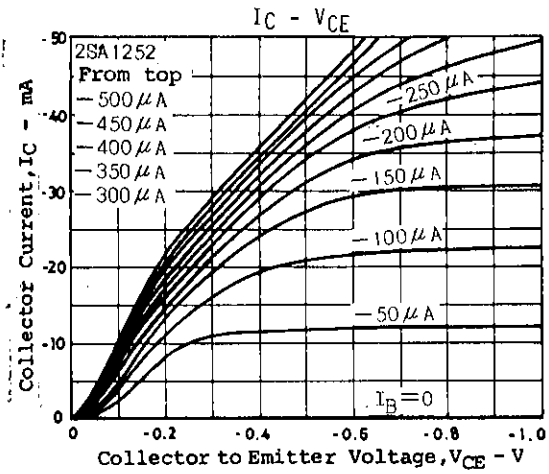
h_{FE} rank : 4,5,6,7

Package Dimensions 2018A

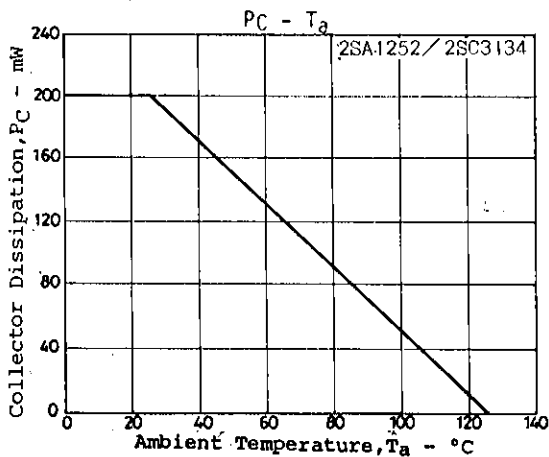
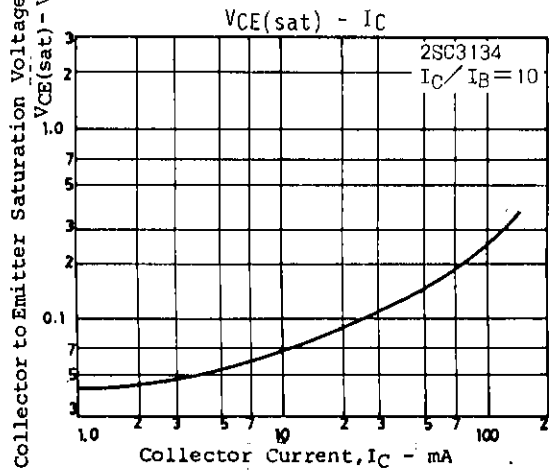
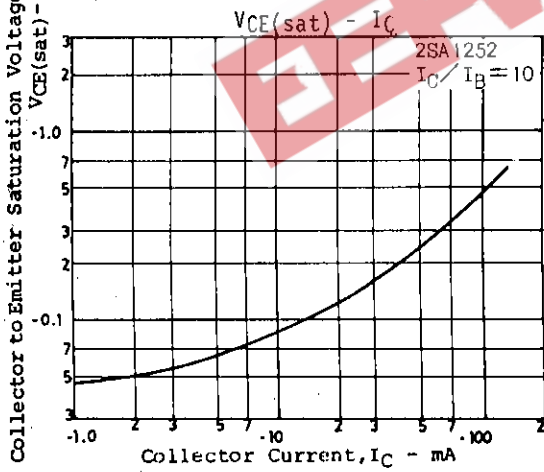
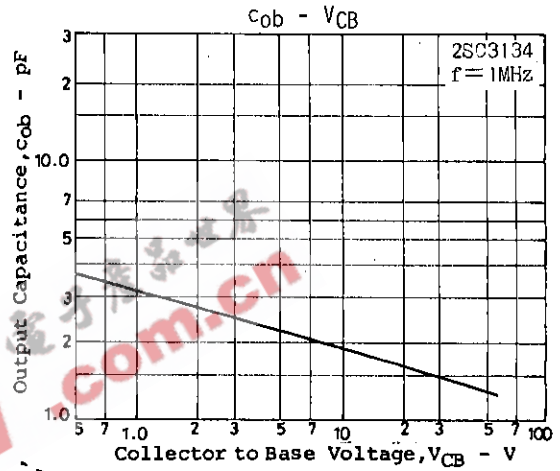
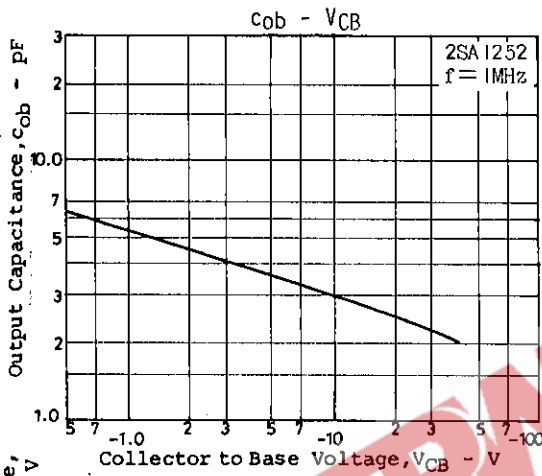
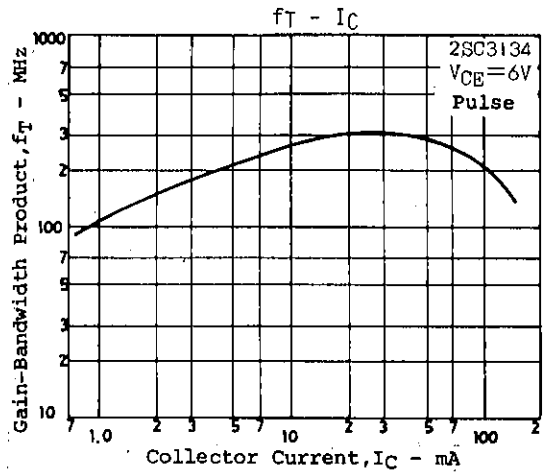
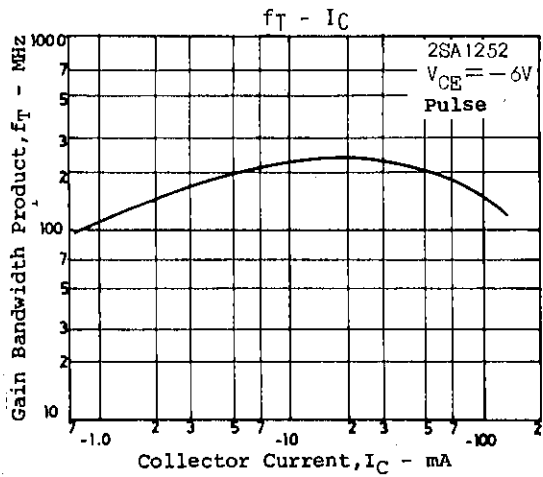
(unit:mm)



2SA1252/2SC3134



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